

## Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D$
20V	250mΩ@4.5V	0.75A
	350mΩ@2.5V	

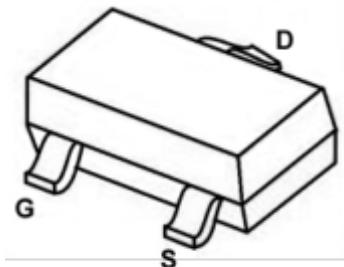
## Feature

- Surface Mount Package
- N-Channel Switch with Low RDS(on)
- Operated at Low Logic Level Gate Drive
- ESD Protected: HBM 2kV

## Applications

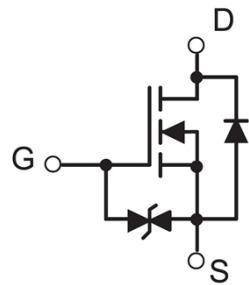
- Load/Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics
- Logic Level Shift

## Package

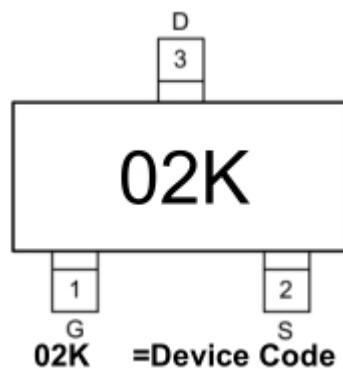


SOT-323

## Circuit diagram



## Marking



## Absolute maximum ratings

( $T_a=25^\circ\text{C}$  unless otherwise noted)

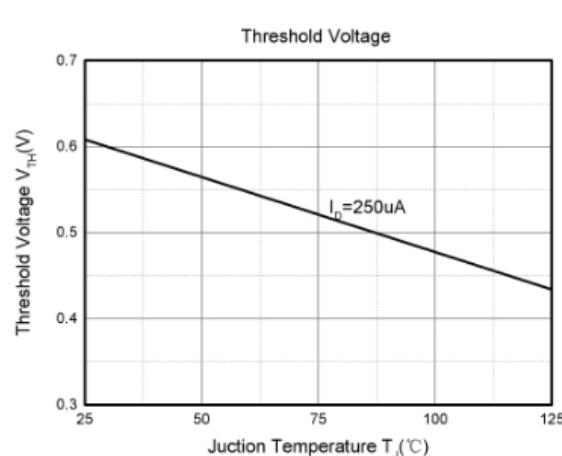
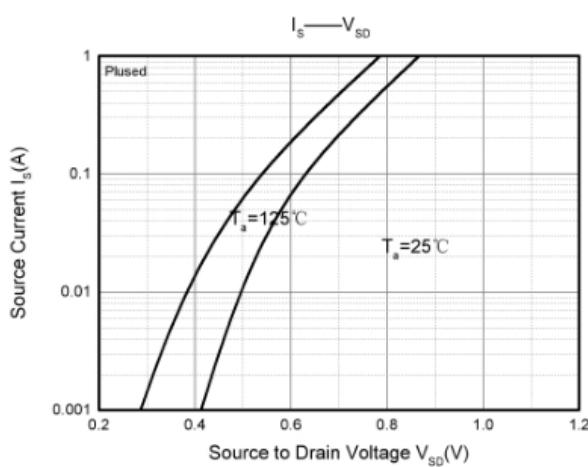
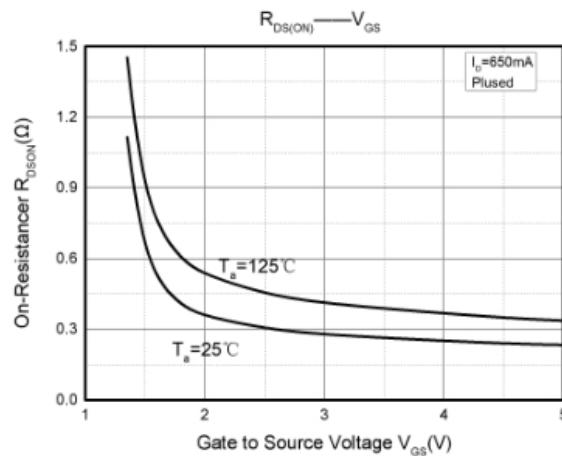
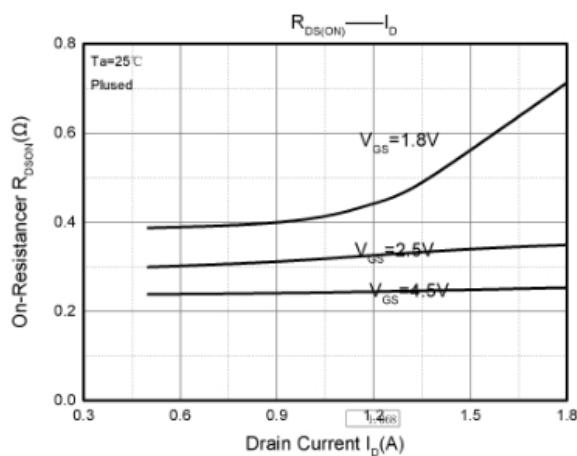
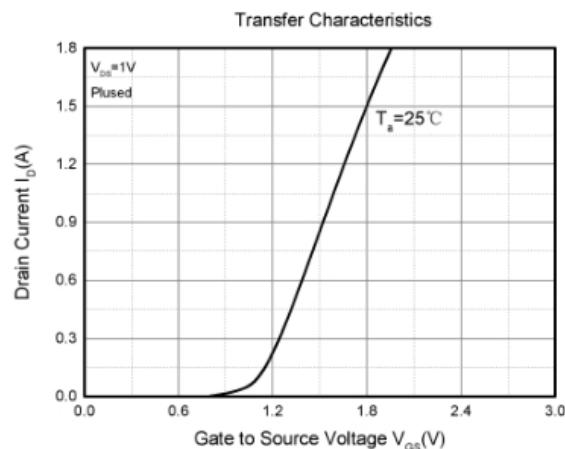
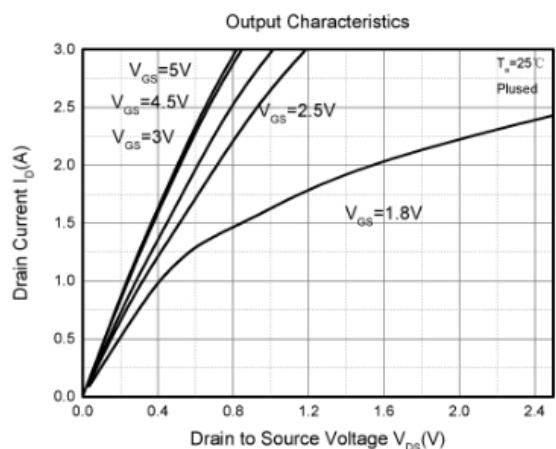
Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Continuous Drain Current	$I_D$	0.75	A
Pulsed Drain Current	$I_{DM}$	1.8	A
Power Dissipation	$P_D$	0.2	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	625	$^\circ\text{C}/\text{W}$
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature	$T_{STG,,}$	-55~+150	$^\circ\text{C}$

## Electrical characteristics

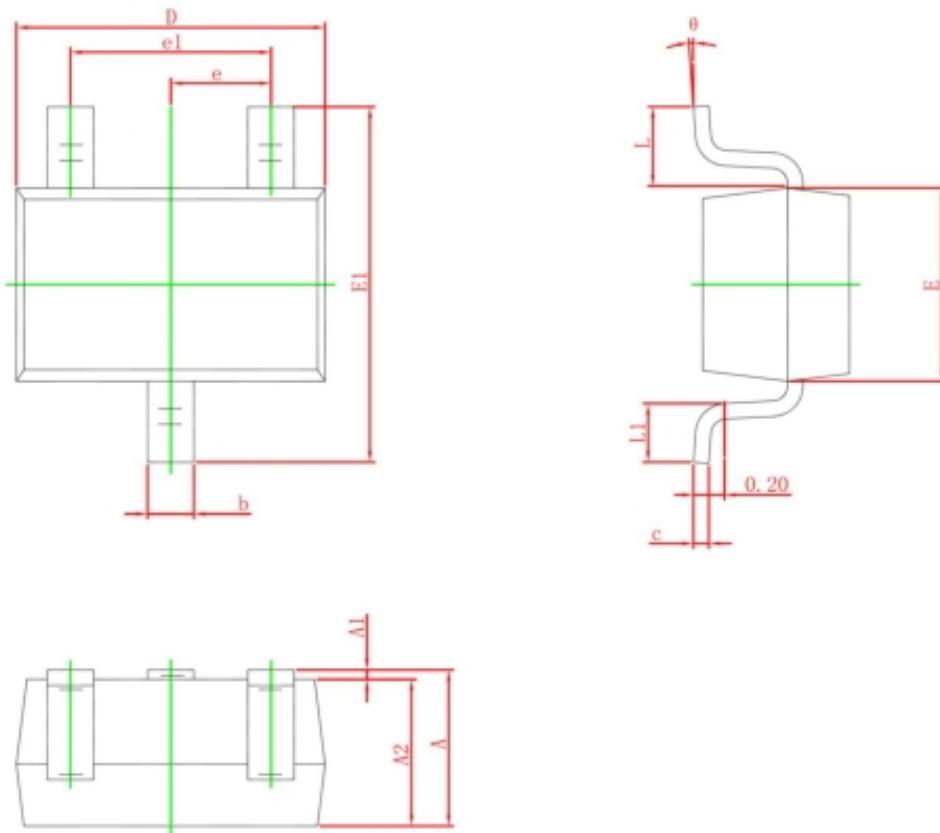
( $T_A=25^\circ\text{C}$ , unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
Drain-source breakdown voltage	$\text{BV}_{(\text{BR})\text{DSS}}$	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$	20			V
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 16\text{V}, V_{GS} = 0\text{V}$			1	$\mu\text{A}$
Gate-body leakage current	$I_{GSS}$	$V_{GS} = \pm 10\text{V}, V_{DS} = 0\text{V}$			$\pm 10$	$\mu\text{A}$
Gate threshold voltage <sup>(1)</sup>	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	0.3	0.65	1	V
Drain-source on-resistance <sup>(1)</sup>	$R_{DS(\text{on})}$	$V_{GS} = 4.5\text{V}, I_D = 0.5\text{A}$		0.25	0.38	$\text{m}\Omega$
		$V_{GS} = 2.5\text{V}, I_D = 0.5\text{A}$		0.35	0.45	
		$V_{GS} = 1.8\text{V}, I_D = 0.5\text{A}$		0.4	0.8	
<b>Dynamic Characteristics</b>						
Input capacitance	$C_{iss}$	$V_{DS} = 16\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$		79	120	$\text{pF}$
Output capacitance	$C_{oss}$			13	20	
Reverse transfer capacitance	$C_{rss}$			9	15	
<b>Switching Parameters</b>						
Turn-on Delay Time	$T_{d(on)}$	$V_{GS} = 4.5\text{V}, V_{DS} = 10\text{V}, I_D = 500\text{mA}, R_{GEN} = 10\Omega$		6.7		$\text{nS}$
Turn-on Rise Time	$T_r$			4.8		
Turn-Off Delay Time	$T_{d(off)}$			17.3		
Turn-Off Fall Time	$t_f$			7.4		
<b>Source-Drain Diode Characteristics</b>						
Body Diode Voltage	$V_{SD}$	$I_S = 0.5\text{A}, V_{GS} = 0\text{V}$		0.7	1.3	V

## Typical Characteristics



## SOT-323 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.000	2.450	0.085	0.096
e	0.650 TYP.		0.026 TYP.	
e1	1.200	1.400	0.047	0.055
L	0.525 REF.		0.021 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°